

# SN74LV574A 3 ステート出力、オクタル・エッジ・トリガ D タイプ・フリップ・フロップ

## 1 特長

- 2V~5.5V の  $V_{CC}$  で動作
- 最大  $t_{pd}$  7.1ns (5V 時)
- 標準  $V_{OLP}$  (出カグラウンド・バウンス)  $< 0.8V$  ( $V_{CC} = 3.3V$ ,  $T_A = 25^\circ C$ )
- 標準  $V_{OHV}$  (出力  $V_{OH}$  アンダーシュート)  $> 2.3V$  ( $V_{CC} = 3.3V$ ,  $T_A = 25^\circ C$ )
- すべてのポートで混在モード電圧動作をサポート
- $I_{off}$  により部分的パワーダウン・モードでの動作をサポート
- JESD 17 準拠で 250mA 超のラッチアップ性能

## 2 アプリケーション

- サーバー
- LED ディスプレイ
- ネットワーク・スイッチ
- 通信インフラ
- モーター・ドライバ
- I/O エクスパンダ

## 3 概要

'LV574A デバイスは、2V~5.5V の  $V_{CC}$  で動作するように設計された、オクタル・エッジ・トリガ型 D タイプ・フリップ・フロップです。

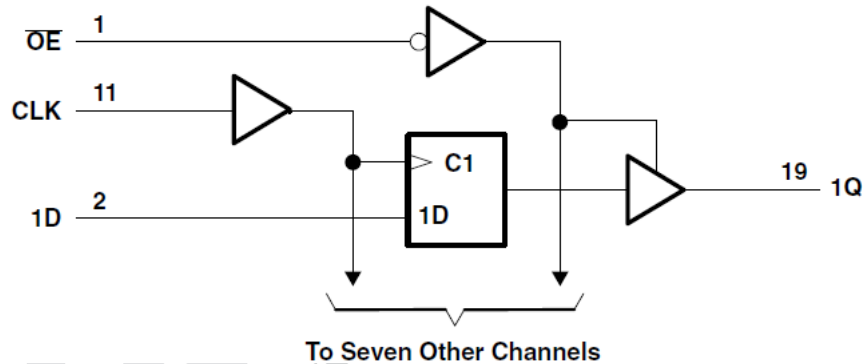
これらのデバイスは、大きな容量性負荷または比較的低いインピーダンスの負荷の駆動用に設計された 3 ステート出力を備えています。本デバイスは、バッファ・レジスタ、I/O ポート、双方向バス・ドライバ、およびワーキング・レジスタの実装に特に適しています。

クロック (CLK) 入力の立ち上がり遷移時に、Q 出力がデータ (D) 入力で設定されたロジック・レベルに設定されます。

### パッケージ情報<sup>(1)</sup>

部品番号	パッケージ	本体サイズ (公称)
SN74LV574A	DB (SSOP, 16)	6.2 × 5.3mm
	DGV (TVSOP, 16)	3.6 × 4.4mm
	DW (SOIC, 16)	10.3 × 7.5mm
	NS (SOP, 16)	10.3 × 5.3mm
	PW (TSSOP, 16)	5 × 4.4mm
	RGY (VQFN, 16)	4 × 3.5mm

(1) 利用可能なすべてのパッケージについては、このデータシートの末尾にある注文情報を参照してください。



論理図 (正論理)



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## 4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

### Changes from Revision J (December 2022) to Revision K (February 2023)

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## 5 Pin Configuration and Functions

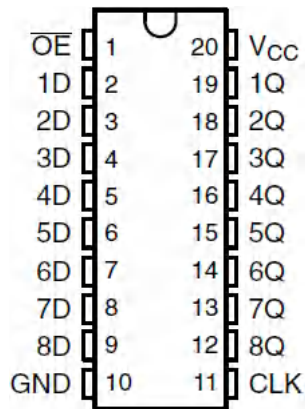


图 5-1. DB, DGV, DW, NS, or PW Package (Top View)

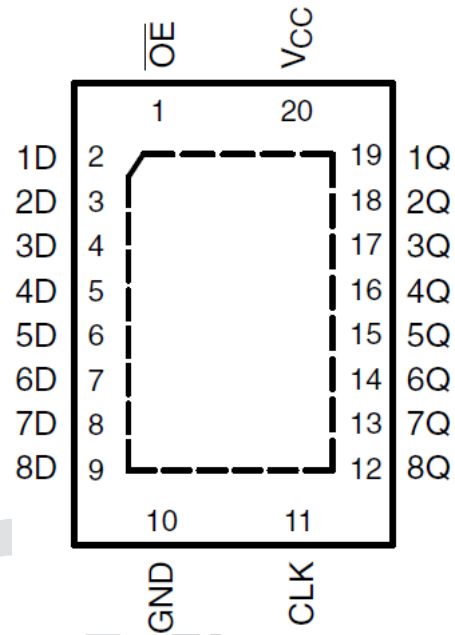


图 5-2. RGY Package (Top View)

表 5-1. Pin Functions

PIN		TYPE	Description
NO.	NAME		
1	$\overline{OE}$	I	Clear all channels, active low
2	1D	I	Channel 1, D input
3	2D	I	Channel 2, D input
4	3D	I	Channel 3, D input
5	4D	I	Channel 4, D input
6	5D	I	Channel 5, D input
7	6D	I	Channel 6, D input
8	7D	I	Channel 7, D input
9	8D	I	Channel 8, D input
10	GND	—	Ground
11	CLK	I	Clock Pin
12	8Q	O	Channel 8, Q output
13	7Q	O	Channel 7, Q output
14	6Q	O	Channel 6, Q output
15	5Q	O	Channel 5, Q output
16	4Q	O	Channel 4, Q output
17	3Q	O	Channel 3, Q output
18	2Q	O	Channel 2, Q output
19	1Q	O	Channel 1, Q output
20	$V_{CC}$	—	Power Pin

## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage range		-0.5	7	V
V <sub>I</sub>	Input voltage range <sup>(2)</sup>		-0.5	7	V
V <sub>O</sub>	Voltage range applied to any output in the high-impedance or power-off state <sup>(2)</sup>		-0.5	7	V
V <sub>O</sub>	Output voltage range applied in the high or low state <sup>(2) (3)</sup>		-0.5	V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	Input clamp current	V <sub>I</sub> < 0		-20	mA
I <sub>OK</sub>	Output clamp current	V <sub>O</sub> < 0		-50	mA
I <sub>O</sub>	Continuous output current	V <sub>O</sub> = 0 to V <sub>CC</sub>		±35	mA
	Continuous current through V <sub>CC</sub> or GND			±70	mA
T <sub>stg</sub>	Storage temperature range		-65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) This value is limited to 5.5-V maximum.

### 6.2 ESD Ratings

			VALUE	UNIT
V <sub>(ESD)</sub>	Electrostatic discharge	Human-Body Model (A114-A)	±2000	V
		Machine Model (A115-A)	±200	
		Charged-Device Model (C101)	±1000	

### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage	2	5.5	V
V <sub>IH</sub>	High-level input voltage	V <sub>CC</sub> = 2 V	1.5	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	V <sub>CC</sub> × 0.7	
		V <sub>CC</sub> = 3 V to 3.6 V	V <sub>CC</sub> × 0.7	
		V <sub>CC</sub> = 4.5 V to 5.5 V	V <sub>CC</sub> × 0.7	
V <sub>IL</sub>	Low-level input voltage	V <sub>CC</sub> = 2 V	0.5	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	V <sub>CC</sub> × 0.3	
		V <sub>CC</sub> = 3 V to 3.6 V	V <sub>CC</sub> × 0.3	
		V <sub>CC</sub> = 4.5 V to 5.5 V	V <sub>CC</sub> × 0.3	
V <sub>I</sub>	Input voltage	0	5.5	V
V <sub>O</sub>	Output voltage	High or low state	0	V <sub>CC</sub>
		3-state	0	5.5
I <sub>OH</sub>	High-level output current	V <sub>CC</sub> = 2 V	-50	μA
		V <sub>CC</sub> = 2.3 V to 2.7 V	-2	mA
		V <sub>CC</sub> = 3 V to 3.6 V	-8	
		V <sub>CC</sub> = 4.5 V to 5.5 V	-16	
I <sub>OL</sub>	Low-level output current	V <sub>CC</sub> = 2 V	50	μA
		V <sub>CC</sub> = 2.3 V to 2.7 V	2	mA
		V <sub>CC</sub> = 3 V to 3.6 V	8	
		V <sub>CC</sub> = 4.5 V to 5.5 V	16	
Δt/Δv	Input transition rise or fall rate	V <sub>CC</sub> = 2.3 V to 2.7 V	200	ns/V
		V <sub>CC</sub> = 3 V to 3.6 V	100	
		V <sub>CC</sub> = 4.5 V to 5.5 V	20	
T <sub>A</sub>	Operating free-air temperature	-40	125	°C

(1) All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, [Implications of Slow or Floating CMOS Inputs](#).

### 6.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>		SN74LV574A							UNIT
		DB	DGV	DW	GQN	NS	PW	RGY	
		20 PINS	20 PINS	20 PINS	20 PINS	20 PINS	20 PINS	20 PINS	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	70	92	58	78	60	83	37	°C/W

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report ([SPRA953](#)).

## 6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V <sub>CC</sub>	MIN	TYP	MAX	UNIT
V <sub>OH</sub>	I <sub>OH</sub> = –50 μA	2 V to 5.5 V	V <sub>CC</sub> – 0.1			V
	I <sub>OH</sub> = –2 mA	2.3 V	2			
	I <sub>OH</sub> = –8 mA	3 V	2.48			
	I <sub>OH</sub> = –16 mA	4.5 V	3.8			
V <sub>OL</sub>	I <sub>OL</sub> = 50 μA	2 V to 5.5 V			0.1	V
	I <sub>OH</sub> = 2 mA	2.3 V			0.4	
	I <sub>OL</sub> = 8 mA	3 V			0.44	
	I <sub>OL</sub> = 16 mA	4.5 V			0.55	
I <sub>I</sub>	V <sub>I</sub> = 5.5 V or GND	0 to 5.5 V			±1	μA
I <sub>OZ</sub>	V <sub>O</sub> = V <sub>CC</sub> or GND	5.5 V			±5	μA
I <sub>CC</sub>	V <sub>I</sub> = V <sub>CC</sub> or GND, I <sub>O</sub> = 0	5.5 V			20	μA
I <sub>off</sub>	V <sub>I</sub> or V <sub>O</sub> = 0 to 5.5 V	0			5	μA
C <sub>i</sub>	V <sub>I</sub> = V <sub>CC</sub> or GND	3.3 V		1.8		pF

## 6.6 Timing Requirements, V<sub>CC</sub> = 2.5 V ± 0.2 V

over recommended operating free-air temperature range (unless otherwise noted)

			T <sub>A</sub> = 25°C		SN74LV574A		UNIT
			MIN	MAX	MIN	MAX	
t <sub>w</sub>	Pulse duration	CLK high or low	7		7		ns
t <sub>su</sub>	Setup time	High or low before CLK↑	5.5		5.5		
t <sub>h</sub>	Hold time	Data after CLK↑	2		2		

### 6.7 Timing Requirements, $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$

over recommended operating free-air temperature range (unless otherwise noted)

			$T_A = 25^\circ\text{C}$		SN74LV574A		UNIT
			MIN	MAX	MIN	MAX	
$t_w$	Pulse duration	CLK high or low	5		5		ns
$t_{su}$	Setup time	High or low before CLK $\uparrow$	3.5		3.5		
$t_h$	Hold time	Data after CLK $\uparrow$	1.5		1.5		

### 6.8 Timing Requirements, $V_{CC} = 5\text{ V} \pm 0.5\text{ V}$

over recommended operating free-air temperature range (unless otherwise noted)

			$T_A = 25^\circ\text{C}$		SN74LV574A		UNIT
			MIN	MAX	MIN	MAX	
$t_w$	Pulse duration	CLK high or low	5		5		ns
$t_{su}$	Setup time	High or low before CLK $\uparrow$	3.5		3.5		
$t_h$	Hold time	Data after CLK $\uparrow$	1.5		1.5		

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## 6.9 Switching Characteristics, $V_{CC} = 2.5\text{ V} \pm 0.2\text{ V}$

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	$T_A = 25^\circ\text{C}$			SN74LV574A		UNIT
				MIN	TYP	MAX	MIN	MAX	
$f_{\text{max}}$			$C_L = 15\text{ pF}$	60	100		50		MHz
			$C_L = 50\text{ pF}$	50	85		40		
$t_{\text{pd}}$	CLK	Q	$C_L = 15\text{ pF}$		9.6	16.6	1	20	ns
$t_{\text{en}}$	$\overline{\text{OE}}$	Q			9.2	16.1	1	19	
$t_{\text{dis}}$	$\overline{\text{OE}}$	Q			6.5	12.8	1	15	
$t_{\text{pd}}$	CLK	Q	$C_L = 50\text{ pF}$		11.6	19.6	1	23	
$t_{\text{en}}$	$\overline{\text{OE}}$	Q			10.9	19	1	22	
$t_{\text{dis}}$	$\overline{\text{OE}}$	Q			8.4	17.5	1	20	
$t_{\text{sk(o)}}$						2		2	

## 6.10 Switching Characteristics, $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	$T_A = 25^\circ\text{C}$			SN74LV574A		UNIT
				MIN	TYP	MAX	MIN	MAX	
$f_{\text{max}}$			$C_L = 15\text{ pF}$	80	145		65		MHz
			$C_L = 50\text{ pF}$	50	120		45		
$t_{\text{pd}}$	CLK	Q	$C_L = 15\text{ pF}$		6.8	13.2	1	15.5	ns
$t_{\text{en}}$	$\overline{\text{OE}}$	Q			6.4	12.8	1	15	
$t_{\text{dis}}$	$\overline{\text{OE}}$	Q			4.8	13	1	15	
$t_{\text{pd}}$	CLK	Q	$C_L = 50\text{ pF}$		8.1	16.7	1	19	
$t_{\text{en}}$	$\overline{\text{OE}}$	Q			7.7	16.3	1	18.5	
$t_{\text{dis}}$	$\overline{\text{OE}}$	Q			6.1	15	1	17	
$t_{\text{sk(o)}}$						1.5		1.5	

## 6.11 Switching Characteristics, $V_{CC} = 5\text{ V} \pm 0.5\text{ V}$

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	$T_A = 25^\circ\text{C}$			SN74LV574A		UNIT
				MIN	TYP	MAX	MIN	MAX	
$f_{\text{max}}$			$C_L = 15\text{ pF}$	130	205		110		MHz
			$C_L = 50\text{ pF}$	85	175		75		
$t_{\text{pd}}$	CLK	Q	$C_L = 15\text{ pF}$		4.8	8.6	1	10	ns
$t_{\text{en}}$	$\overline{\text{OE}}$	Q			4.6	9	1	10.5	
$t_{\text{dis}}$	$\overline{\text{OE}}$	Q			3.5	9	1	10.5	
$t_{\text{pd}}$	CLK	Q	$C_L = 50\text{ pF}$		5.7	10.6	1	12	
$t_{\text{en}}$	$\overline{\text{OE}}$	Q			5.5	11	1	12.5	
$t_{\text{dis}}$	$\overline{\text{OE}}$	Q			4.1	10.1	1	11.5	
$t_{\text{sk(o)}}$						1		1	

## 6.12 Noise Characteristics

$V_{CC} = 3.3\text{ V}$ ,  $C_L = 50\text{ pF}$ ,  $T_A = 25^\circ\text{C}^{(1)}$

PARAMETER		MIN	TYP	MAX	UNIT
$V_{\text{OL(P)}}$	Quiet output, maximum dynamic $V_{\text{OL}}$		0.7	0.8	V
$V_{\text{OL(V)}}$	Quiet output, minimum dynamic $V_{\text{OL}}$		-0.6	-0.8	V
$V_{\text{OH(V)}}$	Quiet output, minimum dynamic $V_{\text{OH}}$		2.8		V
$V_{\text{IH(D)}}$	High-level dynamic input voltage	2.31			V



$V_{CC} = 3.3\text{ V}$ ,  $C_L = 50\text{ pF}$ ,  $T_A = 25^\circ\text{C}$ <sup>(1)</sup>

PARAMETER		MIN	TYP	MAX	UNIT
$V_{IL(D)}$	Low-level dynamic input voltage			0.99	V

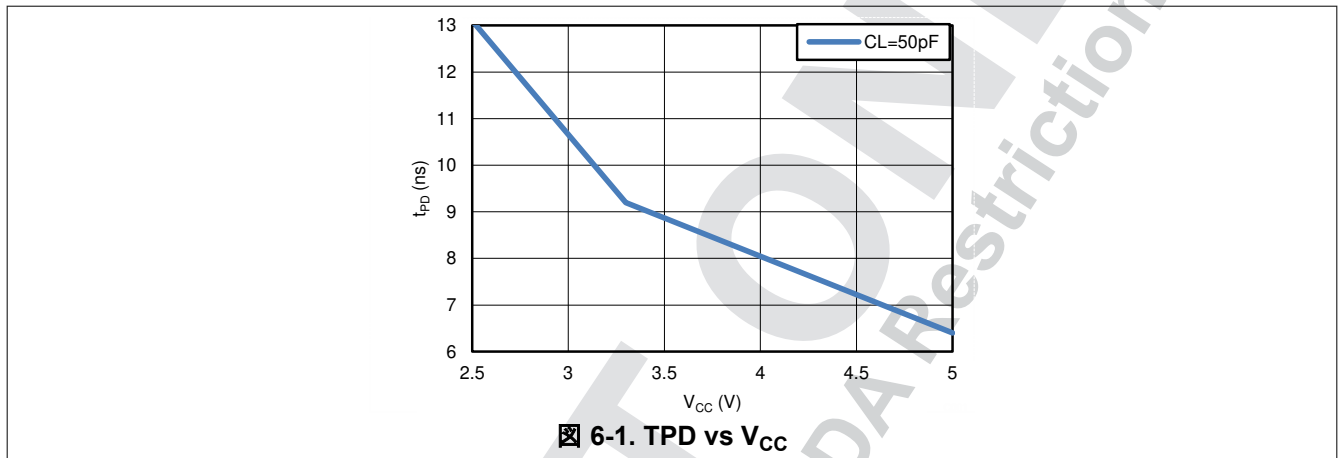
(1) Characteristics are for surface-mount packages only.

### 6.13 Operating Characteristics

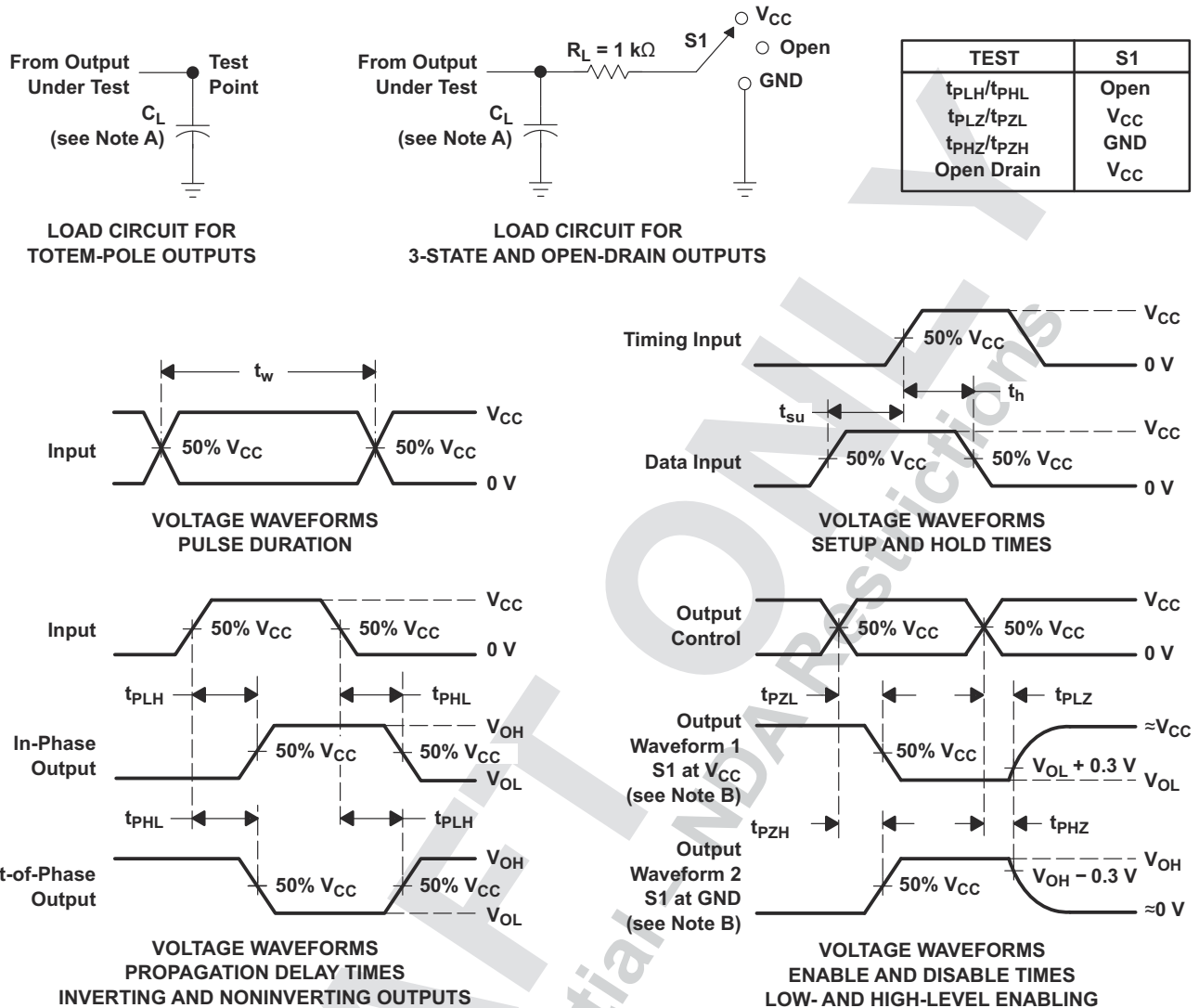
$T_A = 25^\circ\text{C}$

PARAMETER			TEST CONDITIONS		$V_{CC}$	TYP	UNIT
$C_{pd}$	Power dissipation capacitance	Outputs enabled	$C_L = 50\text{ pF}$	$f = 10\text{ MHz}$	3.3 V	20.4	pF
					5 V	23.8	

### 6.14 Typical Characteristics



## 7 Parameter Measurement Information



- A.  $C_L$  includes probe and jig capacitance.
- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics:  $PRR \leq 1 \text{ MHz}$ ,  $Z_O = 50 \Omega$ ,  $t_r \leq 3 \text{ ns}$ ,  $t_f \leq 3 \text{ ns}$ .
- D. The outputs are measured one at a time, with one input transition per measurement.
- E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
- F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
- G.  $t_{PHL}$  and  $t_{PLH}$  are the same as  $t_{pd}$ .
- H. All parameters and waveforms are not applicable to all devices.

**FIG 7-1. Load Circuit and Voltage Waveforms**

## 8 Detailed Description

### 8.1 Overview

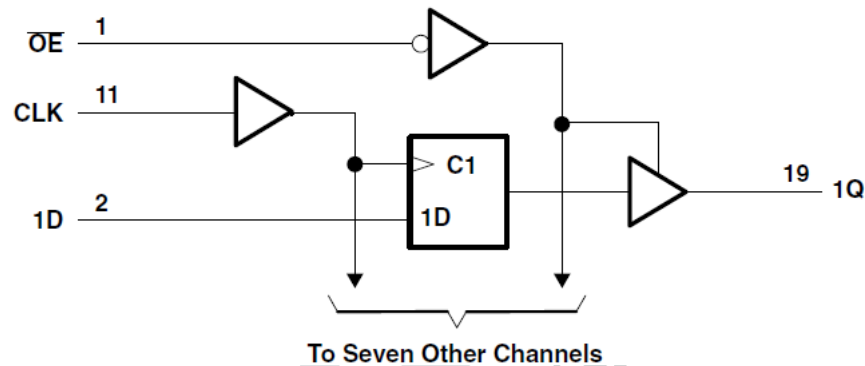
A buffered output-enable (OE) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components.

OE does not affect the internal operations of the flip-flops. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, OE should be tied to  $V_{CC}$  through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

These devices are fully specified for partial-power-down applications using  $I_{off}$ . The  $I_{off}$  circuitry disables the outputs, preventing damaging current backflow through the devices when they are powered down.

### 8.2 Functional Block Diagram




**8-1. Logic Diagram (Positive Logic)**

## 8.3 Feature Description

### 8.3.1 Balanced CMOS 3-State Outputs

This device includes balanced CMOS 3-state outputs. Driving high, driving low, and high impedance are the three states that these outputs can be in. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device can drive larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

When placed into the high-impedance mode, the output will neither source nor sink current, with the exception of minor leakage current as defined in the *Electrical Characteristics* table. In the high-impedance state, the output voltage is not controlled by the device and is dependent on external factors. If no other drivers are connected to the node, then this is known as a floating node and the voltage is unknown. A pull-up or pull-down resistor can be connected to the output to provide a known voltage at the output while it is in the high-impedance state. The value of the resistor will depend on multiple factors, including parasitic capacitance and power consumption limitations. Typically, a 10-k $\Omega$  resistor can be used to meet these requirements.

Unused 3-state CMOS outputs should be left disconnected.

### 8.3.2 Latching Logic

This device includes latching logic circuitry. Latching circuits commonly include D-type latches and D-type flip-flops, but include all logic circuits that act as volatile memory.

When the device is powered on, the state of each latch is unknown. There is no default state for each latch at start-up.

The output state of each latching logic circuit only remains stable as long as power is applied to the device within the supply voltage range specified in the *Recommended Operating Conditions* table.

### 8.3.3 Partial Power Down ( $I_{off}$ )

This device includes circuitry to disable all outputs when the supply pin is held at 0 V. When disabled, the outputs will neither source nor sink current, regardless of the input voltages applied. The amount of leakage current at each output is defined by the  $I_{off}$  specification in the *Electrical Characteristics* table.

### 8.3.4 Clamp Diode Structure

✉ 8-2 shows the inputs and outputs to this device have negative clamping diodes only.

#### 注意

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

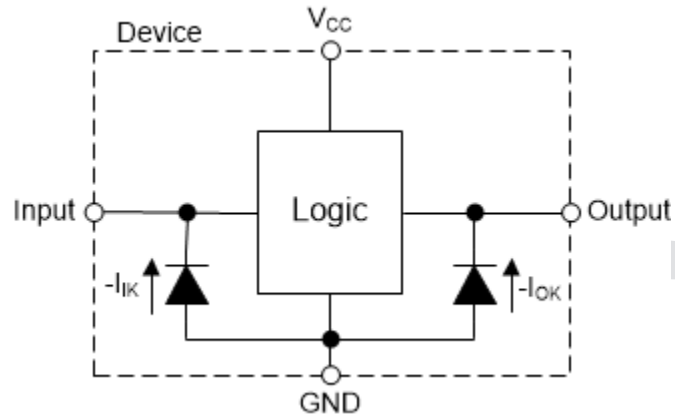


图 8-2. Electrical Placement of Clamping Diodes for Each Input and Output

### 8.4 Device Functional Modes

表 8-1. Function Table

INPUTS <sup>(1)</sup>			OUTPUT Q
$\overline{OE}$	CLK	D	
L	↑	H	H
L	↑	L	L
L	L, H, ↓	X	$Q_0$
H	X	X	Z

(1) H = High Voltage Level, L = Low Voltage Level, X = Do not Care, Z = High Impedance

## 9 Application and Implementation

### 注

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### 9.1 Application Information

The SN74LV574A is a low-drive CMOS device that can be used for a multitude of bus interface type applications where output ringing is a concern. The low drive and slow edge rates will minimize overshoot and undershoot on the outputs. The inputs are 5 V tolerant allowing for down translation to  $V_{CC}$ .

### 9.2 Typical Application

#### 9.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Care should be taken to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads so routing and load conditions should be considered to prevent ringing.

#### 9.2.2 Detailed Design Procedure

1. Add a decoupling capacitor from  $V_{CC}$  to GND. The capacitor needs to be placed physically close to the device and electrically close to both the  $V_{CC}$  and GND pins. An example layout is shown in the *Layout* section.
2. Ensure the capacitive load at the output is  $\leq 50$  pF. This is not a hard limit; it will, however, ensure optimal performance. This can be accomplished by providing short, appropriately sized traces from the SN74LV574A to one or more of the receiving devices.
3. Ensure the resistive load at the output is larger than  $(V_{CC} / I_{O(max)}) \Omega$ . This will ensure that the maximum output current from the *Absolute Maximum Ratings* is not violated. Most CMOS inputs have a resistive load measured in  $M\Omega$ ; much larger than the minimum calculated previously.
4. Thermal issues are rarely a concern for logic gates; the power consumption and thermal increase, however, can be calculated using the steps provided in the application report, [CMOS Power Consumption and Cpd Calculation](#).

#### 9.2.3 Application Curves

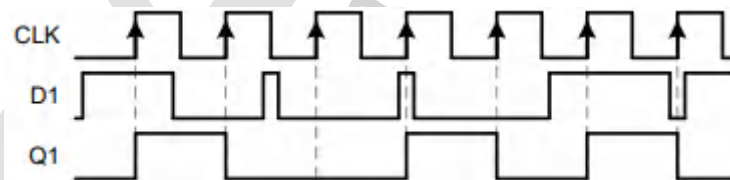


図 9-1. Simplified Functional Diagram Showing Clock Operation

### 9.3 Power Supply Recommendations

The power supply can be any voltage between the MIN and MAX supply voltage rating located in the Recommended Operating Conditions table.

Each  $V_{CC}$  terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1  $\mu\text{F}$  capacitor is recommended. If there are multiple  $V_{CC}$  terminals then 0.01  $\mu\text{F}$  or 0.022  $\mu\text{F}$  capacitors are recommended for each power terminal. It is ok to parallel multiple bypass capacitors to reject different frequencies of noise. 0.1  $\mu\text{F}$  and 1.0  $\mu\text{F}$  capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for the best results.

## 9.4 Layout

### 9.4.1 Layout Guidelines

When using multiple bit logic devices, inputs should not float. In many cases, functions or parts of functions of digital logic devices are unused. Some examples are when only two inputs of a triple-input AND gate are used, or when only 3 of the 4-buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or VCC, whichever makes more sense for the logic function or is more convenient.

#### 9.4.1.1 Layout Example

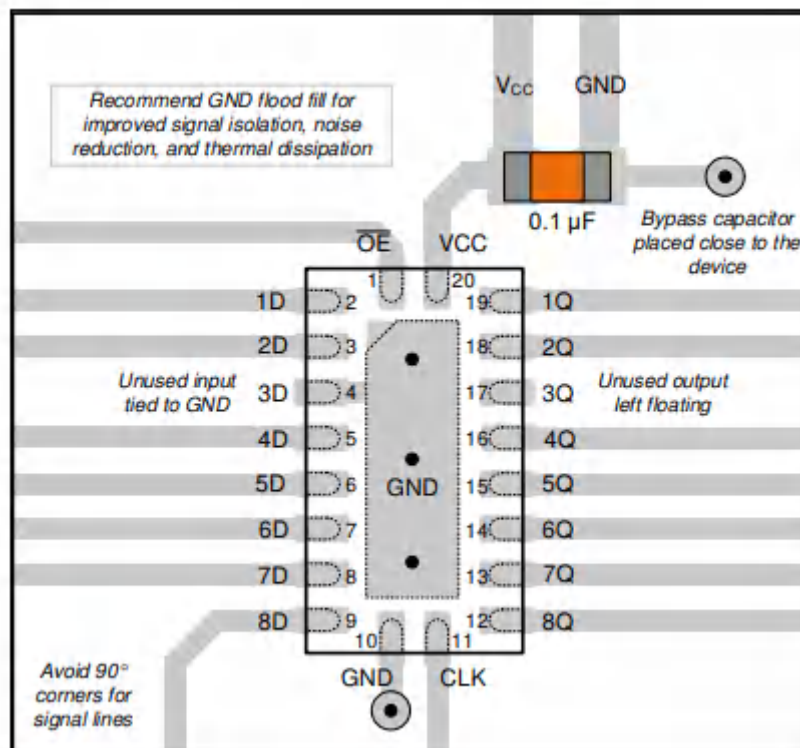


图 9-2. Layout Example for the SN74LV574A in TSSOP

## 10 Device and Documentation Support

### 10.1 Documentation Support

#### 10.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [CMOS Power Consumption and Cpd Calculation application report](#)
- Texas Instruments, [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices application report](#)

#### 10.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on [ti.com](http://ti.com). Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

#### 10.3 Support Resources

TI E2E™ [support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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#### 10.4 Trademarks

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#### 10.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

#### 10.6 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

## 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LV574ADBR	ACTIVE	SSOP	DB	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LV574A	Samples
SN74LV574ADGVR	ACTIVE	TVSOP	DGV	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LV574A	Samples
SN74LV574ADW	OBSOLETE	SOIC	DW	20		TBD	Call TI	Call TI	-40 to 85	LV574A	
SN74LV574ADWR	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LV574A	Samples
SN74LV574ANSR	ACTIVE	SOP	NS	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	74LV574A	Samples
SN74LV574APW	OBSOLETE	TSSOP	PW	20		TBD	Call TI	Call TI	-40 to 85	LV574A	
SN74LV574APWR	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LV574A	Samples
SN74LV574APWT	OBSOLETE	TSSOP	PW	20		TBD	Call TI	Call TI	-40 to 85	LV574A	
SN74LV574ARGYR	ACTIVE	VQFN	RGY	20	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	LV574A	Samples

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

<sup>(6)</sup> Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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**TAPE AND REEL INFORMATION**

**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LV574ADBR	SSOP	DB	20	2000	330.0	16.4	8.2	7.5	2.5	12.0	16.0	Q1
SN74LV574ADGVR	TVSOP	DGV	20	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74LV574ADWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
SN74LV574ANSR	SOP	NS	20	2000	330.0	24.4	8.4	13.0	2.5	12.0	24.0	Q1
SN74LV574APWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1
SN74LV574ARGYR	VQFN	RGY	20	3000	330.0	12.4	3.8	4.8	1.6	8.0	12.0	Q1

**TAPE AND REEL BOX DIMENSIONS**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LV574ADBR	SSOP	DB	20	2000	356.0	356.0	35.0
SN74LV574ADGVR	TVSOP	DGV	20	2000	356.0	356.0	35.0
SN74LV574ADWR	SOIC	DW	20	2000	367.0	367.0	45.0
SN74LV574ANSR	SOP	NS	20	2000	367.0	367.0	45.0
SN74LV574APWR	TSSOP	PW	20	2000	356.0	356.0	35.0
SN74LV574ARGYR	VQFN	RGY	20	3000	356.0	356.0	35.0

# DB0020A



# PACKAGE OUTLINE

## SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



### NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-150.

# EXAMPLE BOARD LAYOUT

DB0020A

SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE: 10X



4214851/B 08/2019

NOTES: (continued)

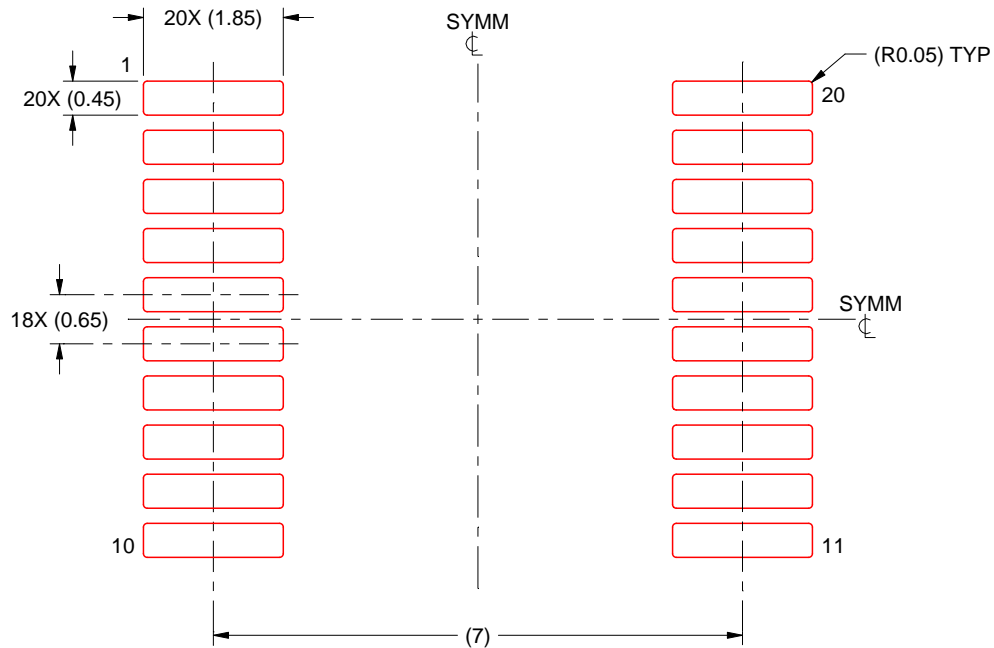
- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

DB0020A

SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL  
SCALE: 10X

4214851/B 08/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.



# MECHANICAL DATA

NS (R-PDSO-G\*\*)

PLASTIC SMALL-OUTLINE PACKAGE

14-PINS SHOWN



- NOTES:
- A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.

DGV (R-PDSO-G\*\*)

PLASTIC SMALL-OUTLINE

24 PINS SHOWN



- NOTES: A. All linear dimensions are in millimeters.  
 B. This drawing is subject to change without notice.  
 C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15 per side.  
 D. Falls within JEDEC: 24/48 Pins – MO-153  
 14/16/20/56 Pins – MO-194

## GENERIC PACKAGE VIEW

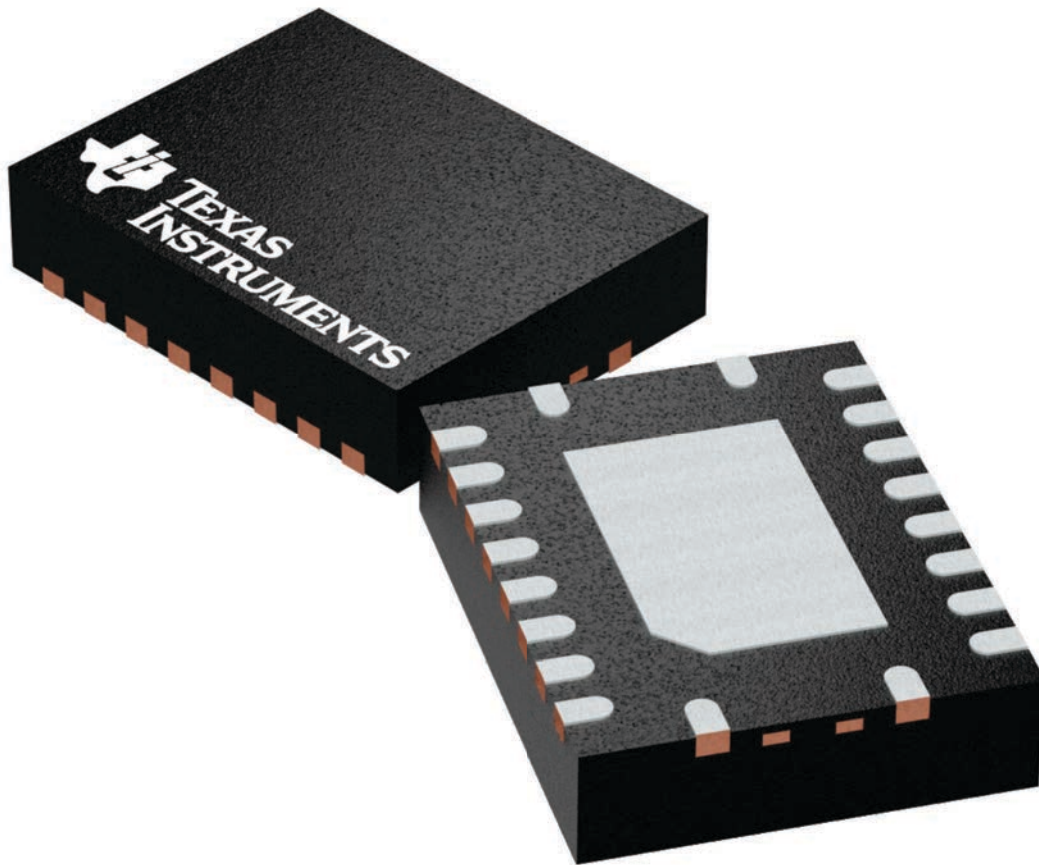
**RGY 20**

**VQFN - 1 mm max height**

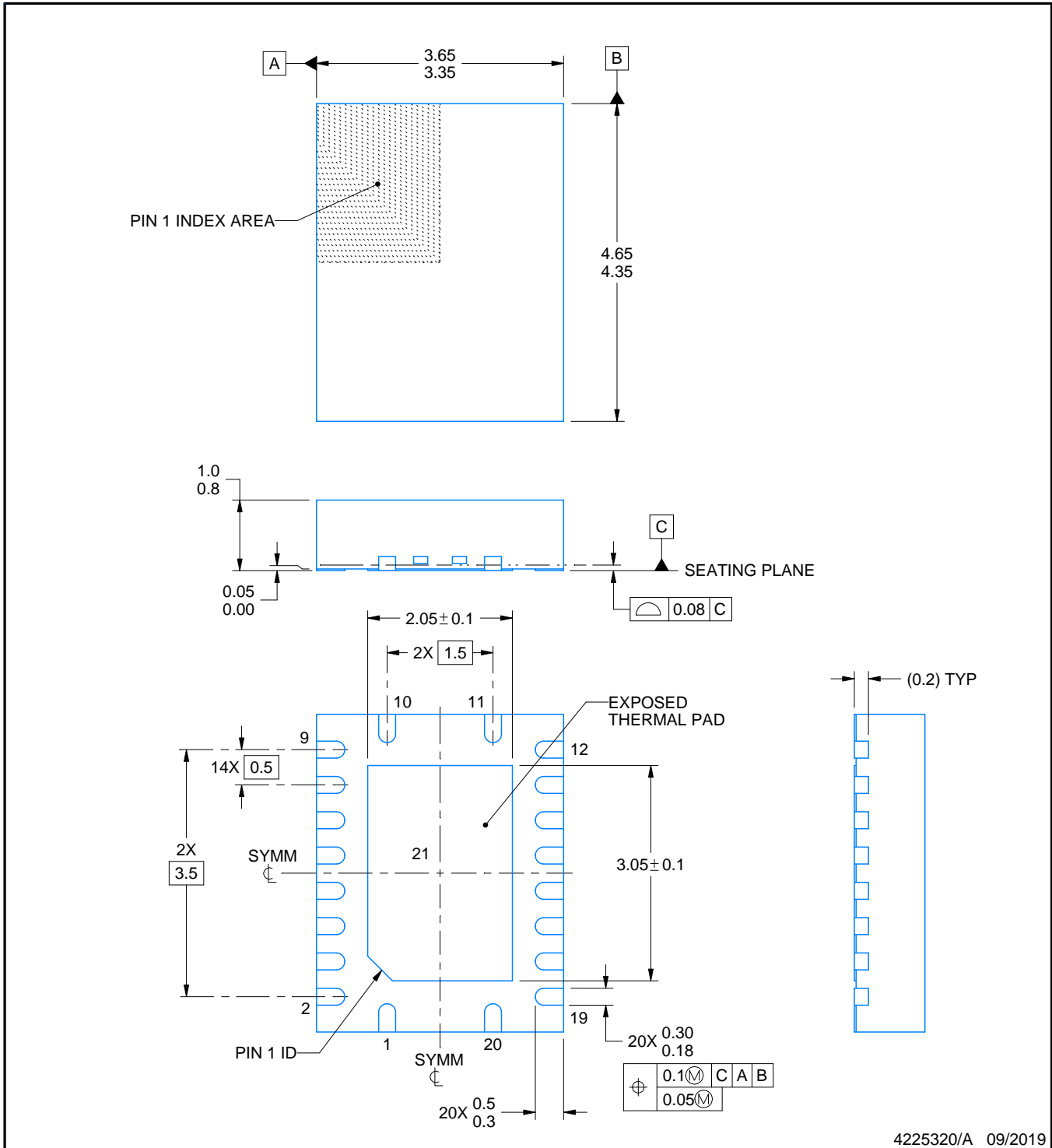
3.5 x 4.5, 0.5 mm pitch

PLASTIC QUAD FGLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary.  
Refer to the product data sheet for package details.



4225264/A



4225320/A 09/2019

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

# EXAMPLE BOARD LAYOUT

RGY0020A

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



**LAND PATTERN EXAMPLE**  
EXPOSED METAL SHOWN  
SCALE:18X



**SOLDER MASK DETAILS**

4225320/A 09/2019

NOTES: (continued)

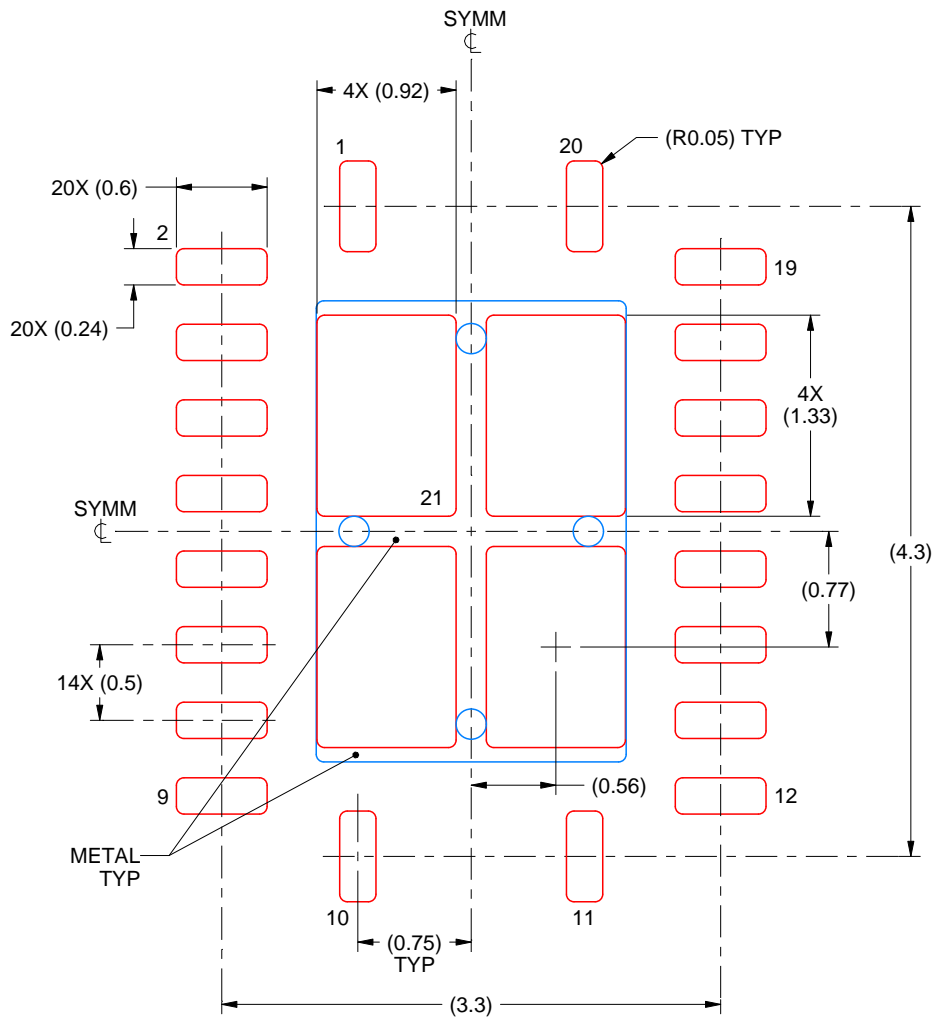
4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 ([www.ti.com/lit/slua271](http://www.ti.com/lit/slua271)).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

# EXAMPLE STENCIL DESIGN

RGY0020A

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



**SOLDER PASTE EXAMPLE**  
 BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD 21  
 78% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE  
 SCALE:20X

4225320/A 09/2019

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

# DW0020A



# PACKAGE OUTLINE

## SOIC - 2.65 mm max height

SOIC



4220724/A 05/2016

**NOTES:**

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
5. Reference JEDEC registration MS-013.

# EXAMPLE BOARD LAYOUT

DW0020A

SOIC - 2.65 mm max height

SOIC



LAND PATTERN EXAMPLE  
SCALE:6X



SOLDER MASK DETAILS

4220724/A 05/2016

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



# EXAMPLE STENCIL DESIGN

DW0020A

SOIC - 2.65 mm max height

SOIC



SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL  
SCALE:6X

4220724/A 05/2016

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

# PW0020A



# PACKAGE OUTLINE

## TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



4220206/A 02/2017

### NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

# EXAMPLE BOARD LAYOUT

PW0020A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE: 10X



SOLDER MASK DETAILS

4220206/A 02/2017

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

PW0020A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL  
SCALE: 10X

4220206/A 02/2017

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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